

Peak pulse voltage (T _j =25 ; non-repetitive, off-state; FIG.8)	V _{pp}	4	kV
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ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol

ORDERING INFORMATION

J	ST	04	V	-800	BW
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}:1A$			
		$V:SOT-223$			$BW:I_{GT1-3} 050 mA$
				$800:V_{DRM}/V_{RRM} 1800 V$	

MARKING

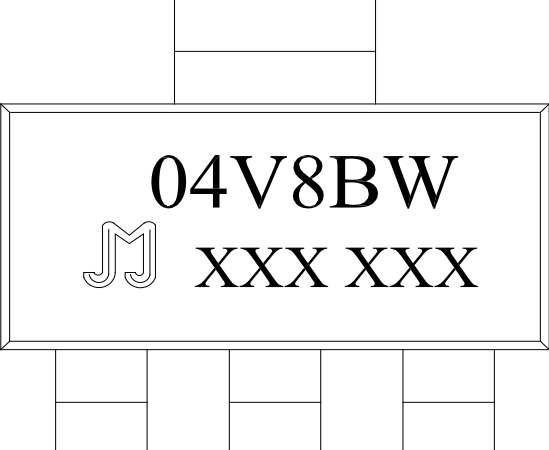
	<u>XXX XXX</u> — LOT NO.
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FIG.1: Maximum power dissipation versus RMS on-state current

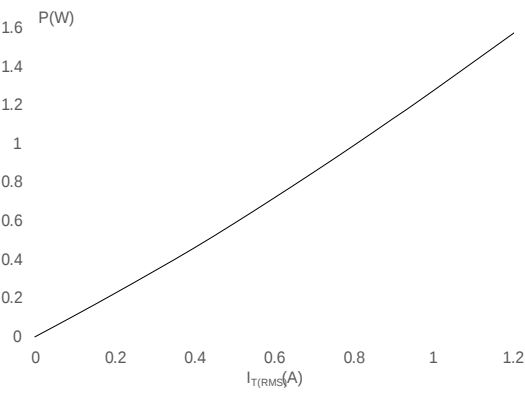


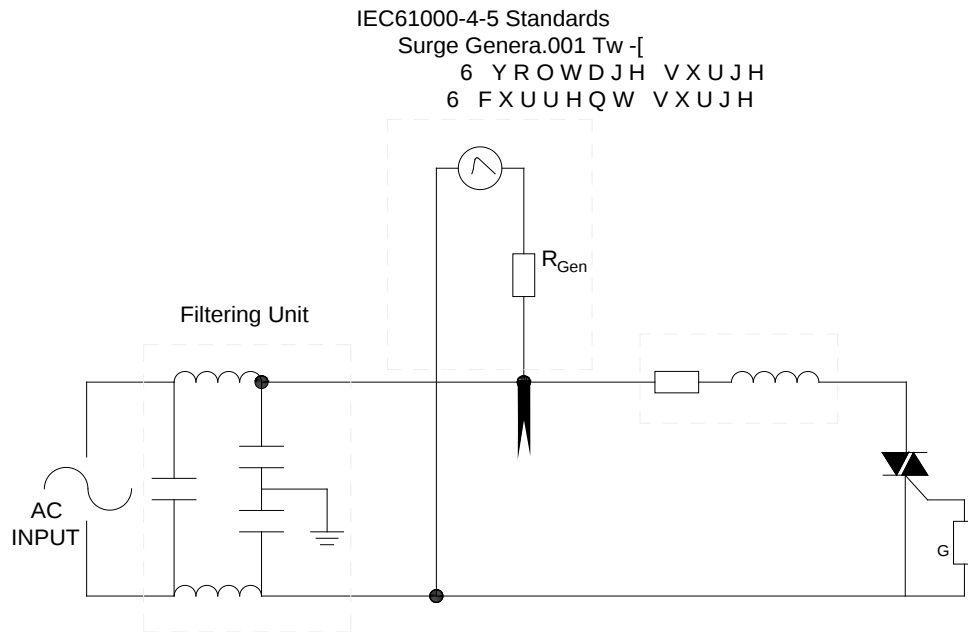
FIG.2: RMS on-state current versus case temperature

0.8

FIG.7: Relative variations of gate trigger current,
holding current and latching current versus
junction temperature



FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



JST04V-800BW

DELIVERY MODE

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W						
E						
F						
D0						
D1						
P0						
P1						
P2						
10P0						
A0						

